Complementary Plastic Silicon Power Transistors

These devices are designed for lower power audio amplifier and low current, high-speed switching applications.

Features

- Low Collector-Emitter Sustaining Voltage
- High Current-Gain Bandwidth Product
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	60	Vdc
Collector-Base Voltage	V _{CBO}	80	Vdc
Emitter Base Voltage	V _{EBO}	6.0	Vdc
Collector Current – Continuous	Ι _C	4.0	Adc
Collector Current – Peak	I _{CM}	8.0	Adc
Base Current – Continuous	Ι _Β	1.0	Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	PD	15 0.12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

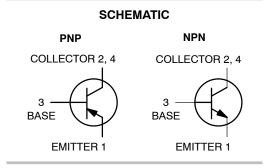
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	8.34	°C/W



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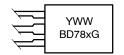
http://onsemi.com

4 AMPERES POWER TRANSISTORS COMPLEMENTARY SILICON 60 VOLTS, 15 WATTS





MARKING DIAGRAM



 $\begin{array}{lll} Y &= Year \\ WW &= Work Week \\ BD78x &= Device Code \\ & x = 7 \ or \ 8 \\ G &= Pb-Free \ Package \end{array}$

ORDERING INFORMATION

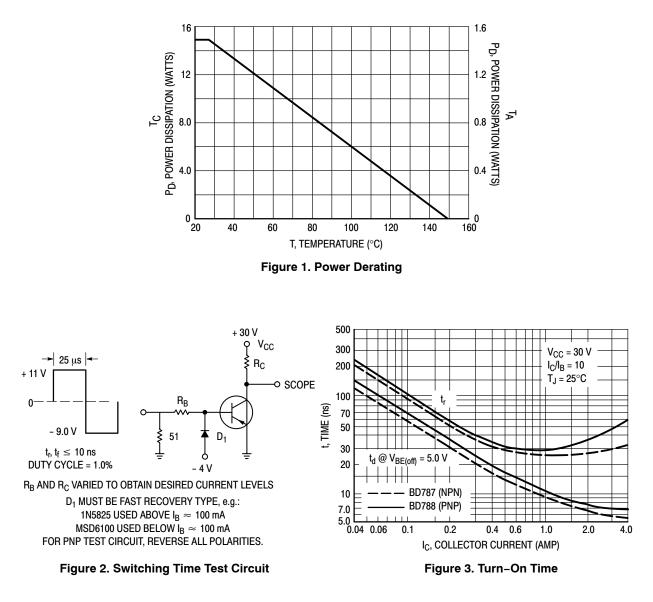
Device	Package	Shipping
BD787G	TO-225 (Pb-Free)	500 Units/Box
BD788G	TO-225 (Pb-Free)	500 Units/Box

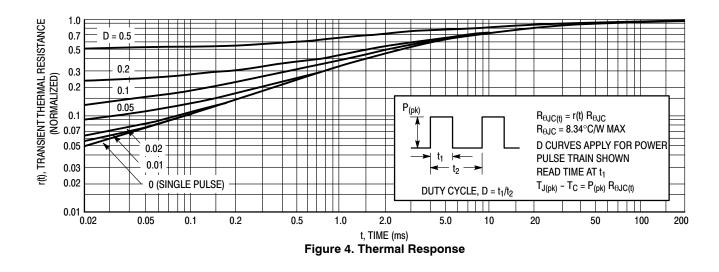
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS* (T_C = 25° C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Sustaining Voltage (Note 1) $(I_{C} = 10 \text{ mAdc}, I_{B} = 0)$		V _{CEO(sus)}	60	-	Vdc
Collector Cutoff Current $(V_{CE} = 20 \text{ Vdc}, I_B = 0)$ $(V_{CE} = 30 \text{ Vdc}, I_B = 0)$		I _{CEO}	-	100	μAdc
$ Collector Cutoff Current \\ (V_{CE} = 80 Vdc, V_{BE(off)} = 1.5 Vdc) \\ (V_{CE} = 40 Vdc, V_{BE(off)} = 1.5 Vdc, T_C = 125^{\circ}C) $		ICEX		1.0 0.1	μAdc mAdc
Emitter Cutoff Current ($V_{EB} = 6.0 \text{ Vdc}, I_C = 0$)		I _{EBO}	-	1.0	μAdc
ON CHARACTERISTICS (Note 1)			•		
$ \begin{array}{l} \mbox{DC Current Gain} \\ (I_C = 200 \mbox{ mAdc}, V_{CE} = 3.0 \mbox{ Vdc}) \\ (I_C = 1.0 \mbox{ Adc}, V_{CE} = 3.0 \mbox{ Vdc}) \\ (I_C = 2.0 \mbox{ Adc}, V_{CE} = 3.0 \mbox{ Vdc}) \\ (I_C = 4.0 \mbox{ Adc}, V_{CE} = 3.0 \mbox{ Vdc}) \end{array} $		h _{FE}	40 25 20 5.0	250 _ _ _	-
Collector-Emitter Saturation Voltage $(I_{C} = 500 \text{ mAdc}, I_{B} = 50 \text{ mAdc})$ $(I_{C} = 1.0 \text{ Adc}, I_{B} = 100 \text{ mAdc})$ $(I_{C} = 2.0 \text{ Adc}, I_{B} = 200 \text{ mAdc})$ $(I_{C} = 4.0 \text{ Adc}, I_{B} = 800 \text{ mAdc})$		V _{CE(sat)}	- - - -	0.4 0.6 0.8 2.5	Vdc
Base–Emitter Saturation Voltage $(I_C = 2.0 \text{ Adc}, I_B = 200 \text{ mAdc})$		V _{BE(sat)}	-	2.0	Vdc
Base–Emitter On Voltage (I_C = 2.0 Adc, V_{CE} = 3.0 Vdc)		V _{BE(on)}	_	1.8	Vdc
DYNAMIC CHARACTERISTICS		·			
Current–Gain – Bandwidth Product (I _C = 100 mAdc, V _{CE} = 10 Vdc, f = 10 MHz)		f _T	50	-	MHz
Output Capacitance $(V_{CB} = 10 \text{ Vdc}, I_C = 0)$ (f = 0.1 MHz)	BD787 BD788	C _{ob}		50 70	pF
Small–Signal Current Gain (I _C = 200 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)		h _{fe}	10	-	-

*Indicates JEDEC Registered Data 1. Pulse Test; Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%.





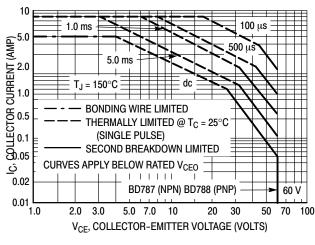


Figure 5. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150^{\circ}$ C: T_{C} is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 150^{\circ}$ C, $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

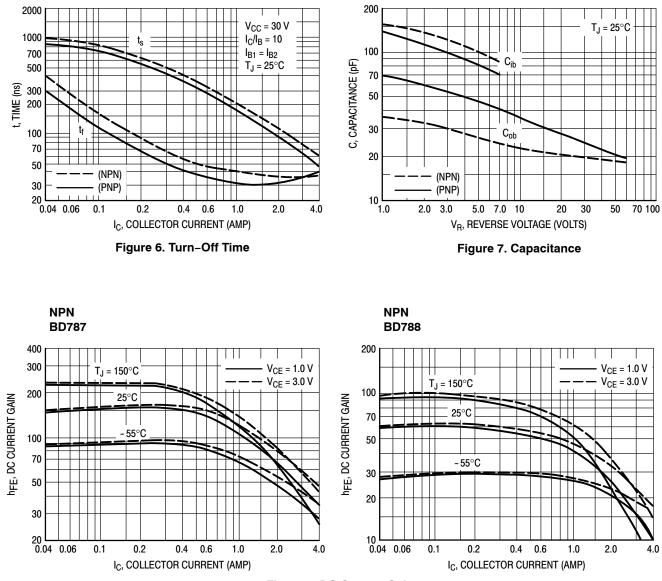
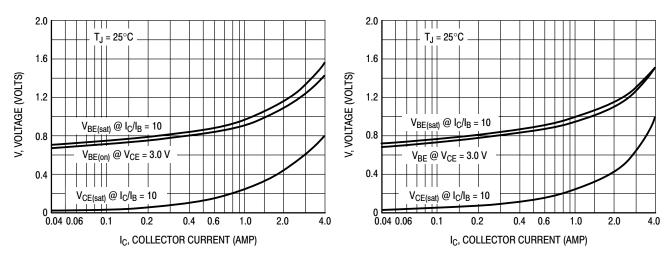
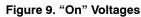
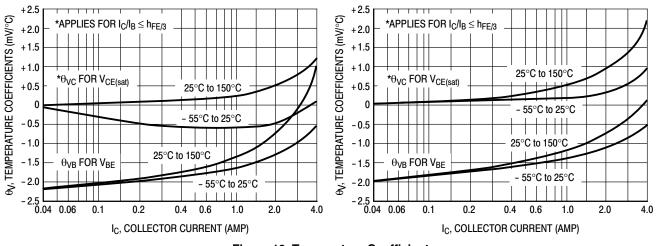


Figure 8. DC Current Gain



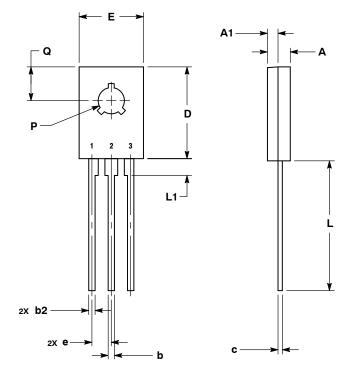






PACKAGE DIMENSIONS

TO-225 CASE 77-09 **ISSUE AA**



NOTES:

1. DIMENSIONING AND TOLERANCING PER

ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: MILLIMETERS. 3. NUMBER AND SHAPE OF LUGS OPTIONAL.

	_		
	MILLIMETERS		
DIM	MIN MAX		
Α	2.40	3.00	
A1	1.00	1.50	
b	0.60	0.90	
b2	0.51	0.88	
C	0.39	0.63	
D	10.60	11.10	
Е	7.40	7.80	
е	2.04	2.54	
L	14.50	16.63	
L1	1.27	2.54	
Р	2.90	3.30	
Q	3.80	4.20	

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